1. General description

NPN high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9560Z

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- · High collector current capability
- High collector current gain h_{FE} at high I_C
- AEC-Q101 qualified

3. Applications

- · Electronic ballast for fluorescent lighting
- · LED driver for LED chain module
- LCD backlighting
- · High Intensity Discharge (HID) front lighting
- Automotive motor management
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	600	V
I _C	collector current		-	-	0.5	Α
h _{FE}	DC current gain	$V_{CE} = 10 \text{ V}; I_{C} = 50 \text{ mA}; T_{amb} = 25 \text{ °C}$	70	135	-	



600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	2, 4
2	С	collector		. 🗸
3	Е	emitter		1—
4	С	collector	□1 □2 □3	3
			SC-73 (SOT223)	sym016

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBHV8560Z		plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223			

7. Marking

Table 4. Marking codes

Type number	Marking code
PBHV8560Z	HV856Z

600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

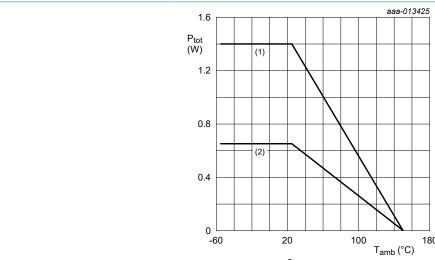
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	600	V
V _{CEO}	collector-emitter voltage	open base		-	600	V
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	600	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	0.5	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.65	W
			[2]	-	1.4	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, standard footprint

Fig. 1. Power derating curves

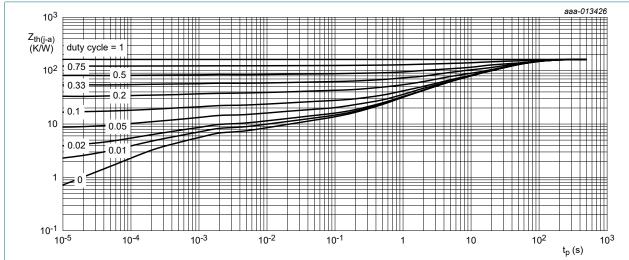
600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

9. Thermal characteristics

Table 6. Thermal characteristics

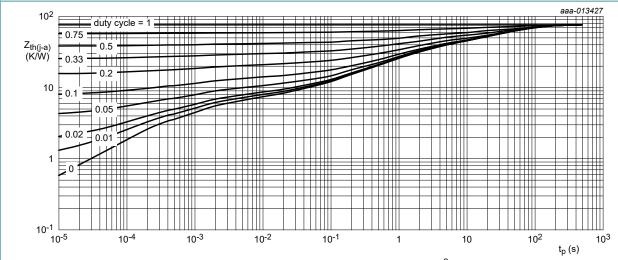
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	-	190	K/W
juncti	junction to ambient		[2]	-	-	89	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



FR4 PCB, single-sided copper, tin-plated and standard footprint.

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 400 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 400 V; I _E = 0 A; T _j = 150 °C	-	-	10	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 400 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 4 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V; I _C = 50 mA; T _{amb} = 25 °C	70	135	-	
		V_{CE} = 10 V; I_{C} = 100 mA; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	70	135	-	
- OLSat	collector-emitter	I _C = 50 mA; I _B = 5 mA; T _{amb} = 25 °C	-	50	100	mV
	saturation voltage	I_C = 100 mA; I_B = 20 mA; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C; pulsed	-	50	100	mV
V _{BEsat}	base-emitter saturation voltage	I_C = 50 mA; I_B = 5 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	950	mV
C _c	collector capacitance	$V_{CB} = 20 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$	-	7.5	-	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 ^{\circ}\text{C}$	-	710	-	pF

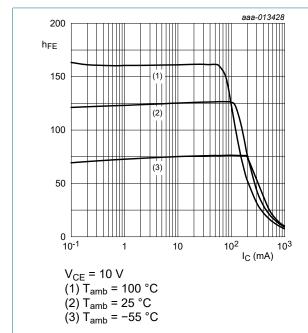


Fig. 4. DC current gain as a function of collector current; typical values

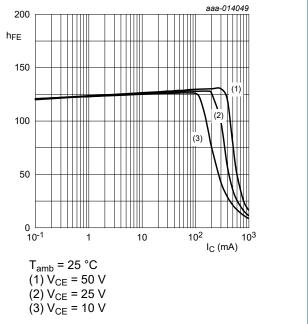


Fig. 5. DC current gain as a function of collector current; typical values

600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

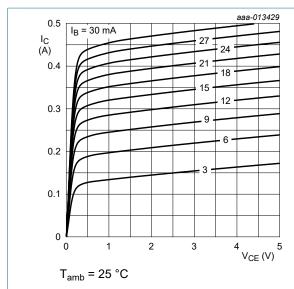
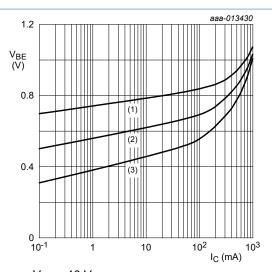
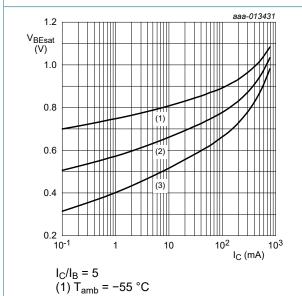


Fig. 6. Collector current as a function of collectoremitter voltage; typical values



V_{CE} = 10 V (1) T_{amb} = -55 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

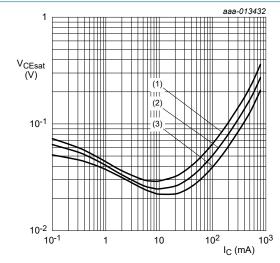
Fig. 7. Base-emitter voltage as a function of collector current; typical values



(3) T_{amb}= 100 °C

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

(2) T_{amb} = 25 °C



 $I_{\rm C}/I_{\rm B} = 5$ (1) $T_{\rm amb} = 100~{\rm ^{\circ}C}$ (2) $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3) $T_{\rm amb} = -55~{\rm ^{\circ}C}$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

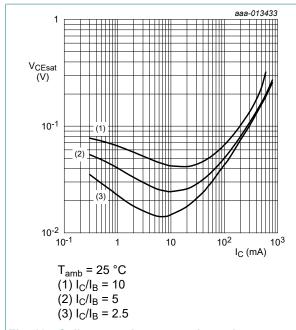


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

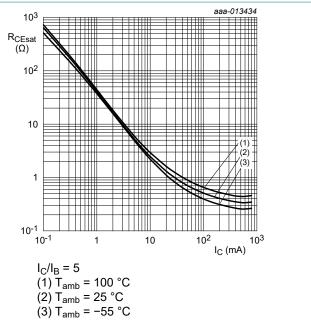
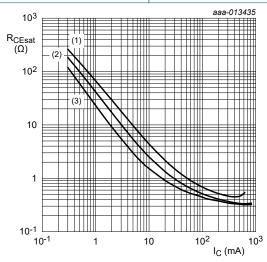


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values



 $T_{amb} = 25 \,^{\circ}C$ (1) $I_C/I_B = 10$ (2) $I_C/I_B = 5$ $(3) I_{\rm C}/I_{\rm B} = 2.5$

Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

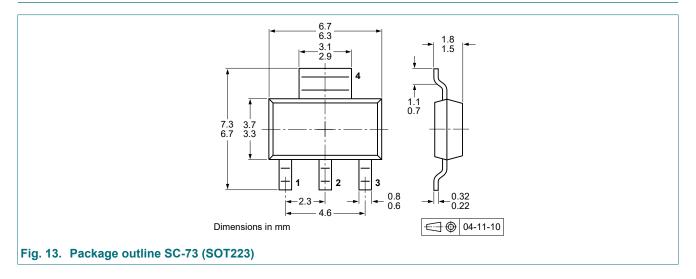
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11. Test information

Quality information

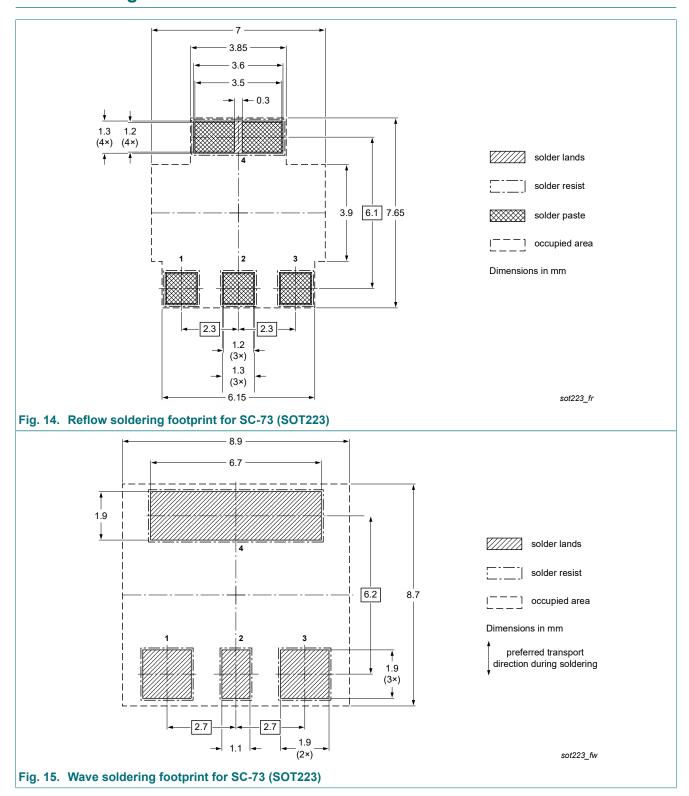
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

13. Soldering



600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBHV8560Z v.2	20200907	Product data sheet	-	PBHV8560Z v.1			
Modifications:	Characteristics:	Characteristics: Legend corrected at Figure 5					
PBHV8560Z v.1	20150313	Product data sheet	-	-			

600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PBHV8560Z

600 V, 0.5 A NPN high-voltage low VCEsat (BISS) transistor

Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	4
10	. Characteristics	5
11.	. Test information	8
12	. Package outline	8
	. Soldering	
	. Revision history	
	. Legal information	

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